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Patent  
Attorney's Docket No. 015290-506

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Patent Application of	)	
	)	
Ting CHIEN et al.	)	Group Art Unit: 1765
	)	
Application No.: 09/820,692	)	Examiner: K.C. Chen
	)	
Filed: March 30, 2001	)	Confirmation No. 5245
	)	
For: PLASMA ETCHING OF DIELECTRIC	)	
LAYER WITH SELECTIVITY TO STOP	)	
LAYER	)	

**AMENDMENT**

Assistant Commissioner for Patents  
Washington, D.C. 20231

Sir:

Reconsideration of the Official Action dated April 10, 2002 is respectfully  
requested.

**IN THE CLAIMS**

A marked-up version of the claims showing insertions and deletions appears in  
Appendix A. Please rewrite Claims 1-3 and 19, and add new Claims 21-22 as follows:

1. (Amended) A method of etching a dielectric layer with selectivity to an  
underlying stop layer, comprising:  
supporting a semiconductor substrate in a plasma etch reactor, the substrate  
including a dielectric layer over a stop layer;

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